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# BT236X-600

4Q Triac

1 May 2015

Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT186A "full pack" plastic package intended for use in general purpose bidirectional switching and phase control applications.

## 2. Features and benefits

- High blocking voltage capability
- Isolated package
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 20 \text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	65	A
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_h \leq 88^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	6	A

### Static characteristics

$I_{GT}$	gate trigger current	$V_D = 12 \text{ V}$ ; $I_T = 0.1 \text{ A}$ ; T2+ G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	5	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 0.1 \text{ A}$ ; T2+ G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	8	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 0.1 \text{ A}$ ; T2- G-; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	11	35	mA
		$V_D = 12 \text{ V}$ ; $I_T = 0.1 \text{ A}$ ; T2- G+; $T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	30	70	mA



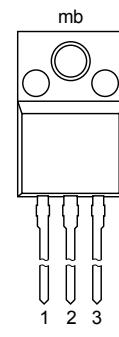
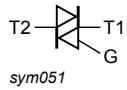
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### 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <b>TO-220F (SOT186A)</b>	 <b>sym051</b>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

### 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BT236X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

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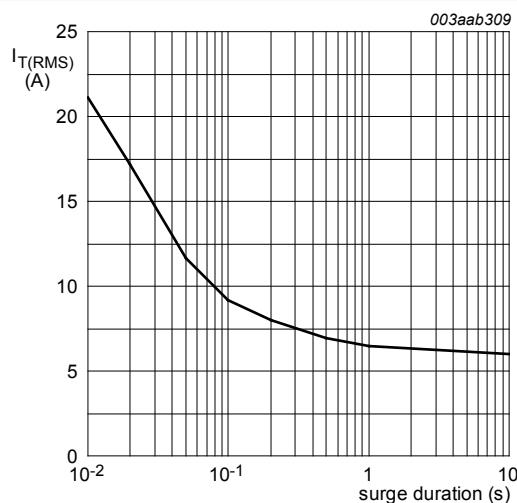
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### 7. Limiting values

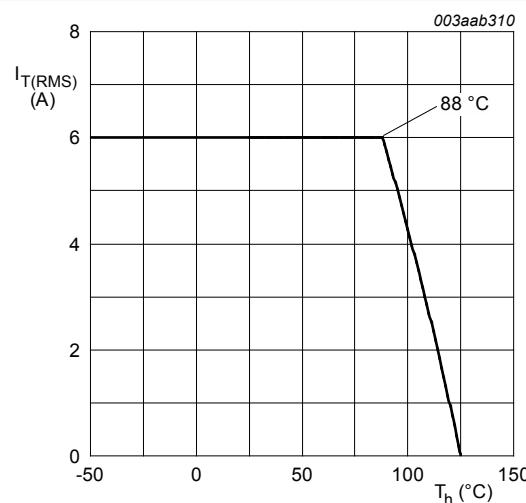
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 88^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 20 \text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	65	A
		full sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 16.7 \text{ ms}$	-	71	A
$I^2t$	$I^2t$ for fusing	$t_p = 10 \text{ ms}$ ; SIN	-	21	$\text{A}^2\text{s}$
$dI_T/dt$	rate of rise of on-state current	$I_G = 70 \text{ mA}$ ; T2+ G+	-	50	$\text{A}/\mu\text{s}$
		$I_G = 70 \text{ mA}$ ; T2+ G-	-	50	$\text{A}/\mu\text{s}$
		$I_G = 140 \text{ mA}$ ; T2- G+	-	10	$\text{A}/\mu\text{s}$
		$I_G = 70 \text{ mA}$ ; T2- G-	-	50	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values**

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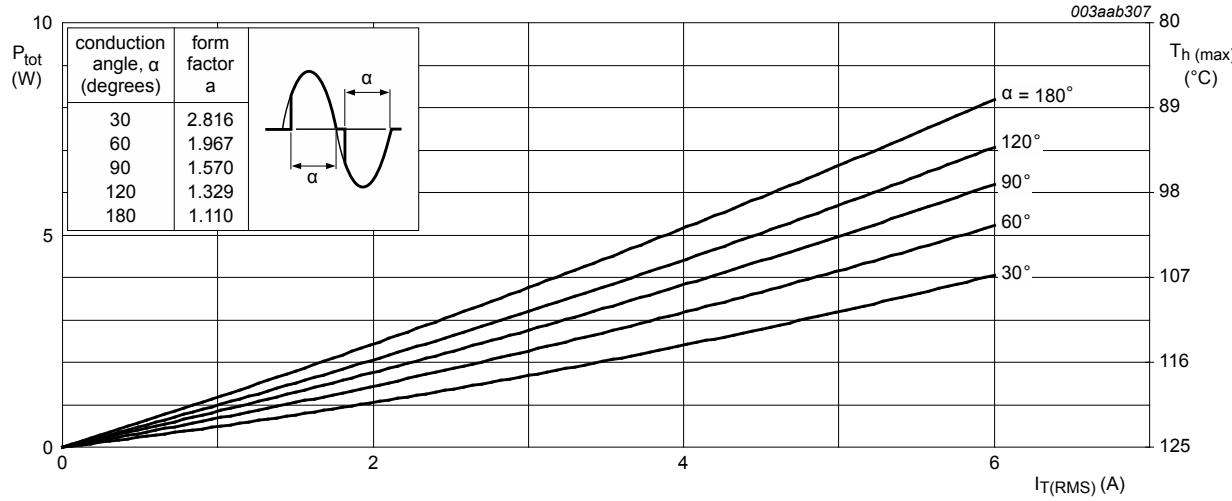


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

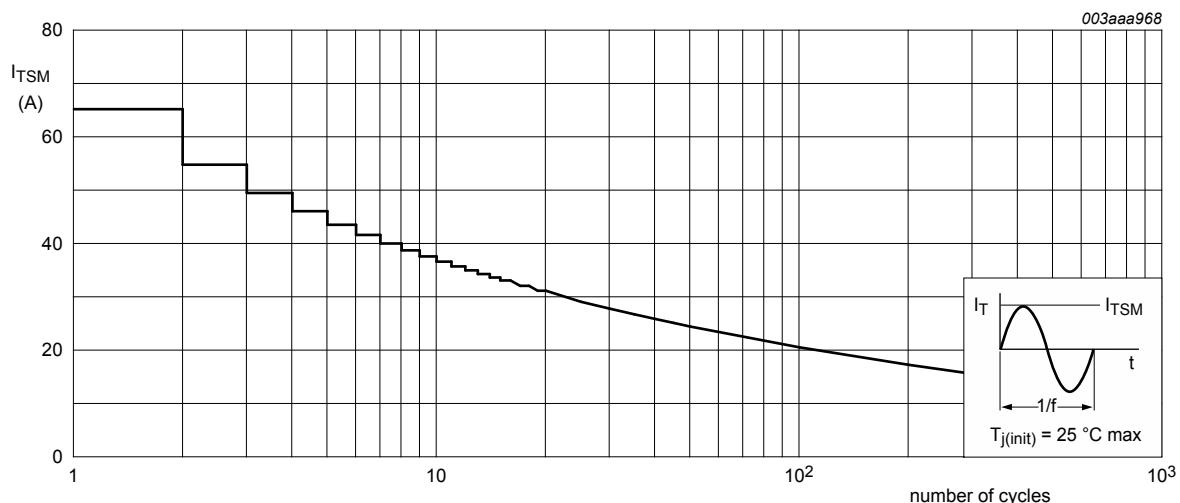


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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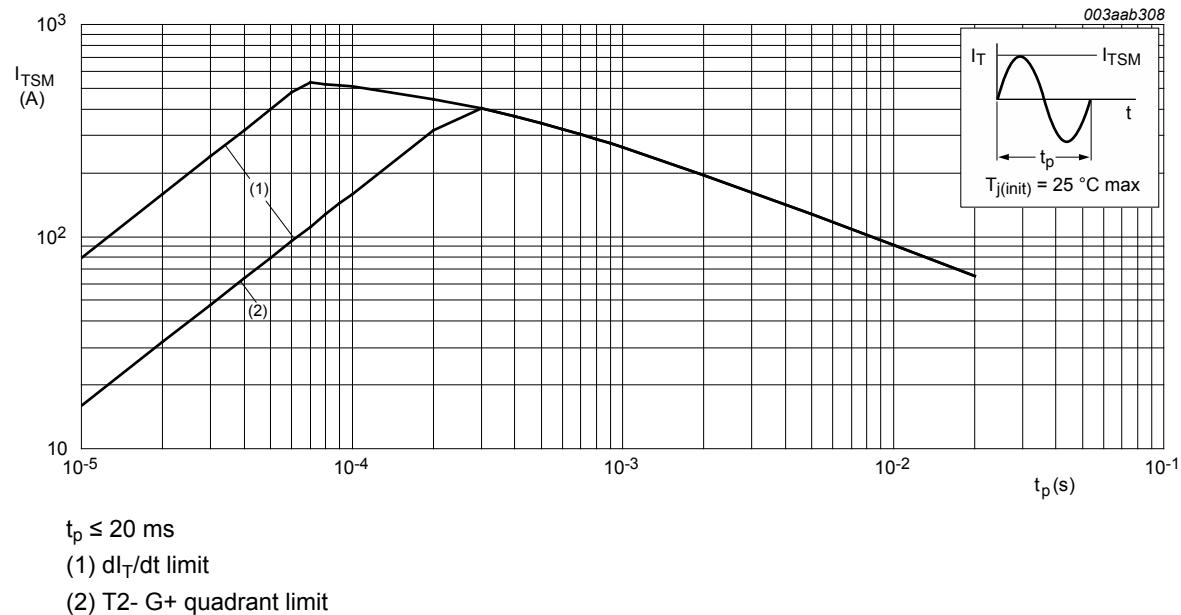


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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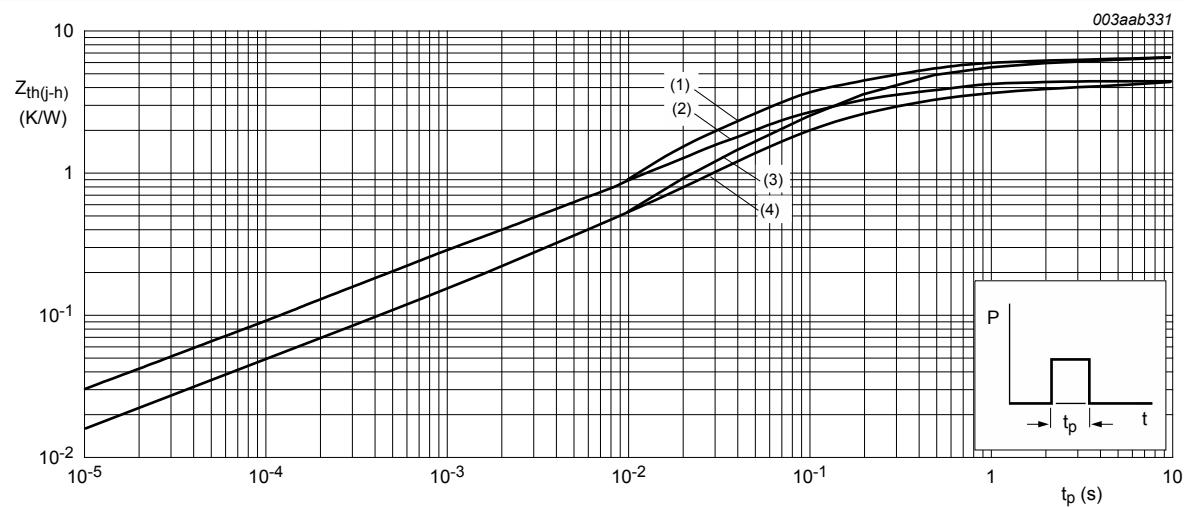
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## 8. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; without heatsink compound; <a href="#">Fig. 6</a>	-	-	4.5	K/W
		full or half cycle; with heatsink compound; <a href="#">Fig. 6</a>				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

**Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width**

## 9. Isolation characteristics

**Table 6. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50 \text{ Hz} \leq f \leq 60 \text{ Hz}$ ; $\text{RH} \leq 65\%$ ; $T_h = 25^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink; $f = 1 \text{ MHz}$ ; $T_h = 25^\circ\text{C}$	-	10	-	pF

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### 10. Characteristics

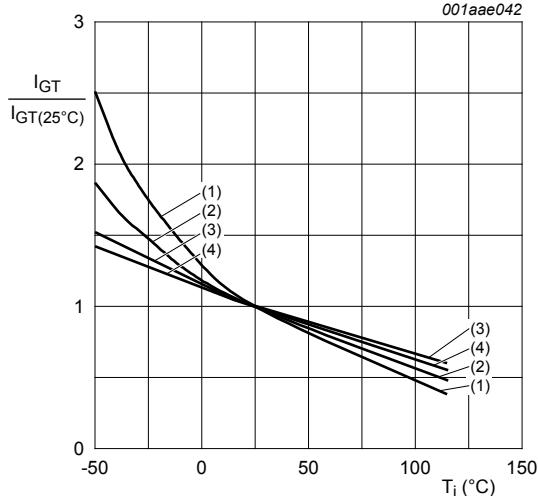
**Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	5	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	8	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	11	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	30	70	mA
I <sub>L</sub>	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>		-	7	30	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>		-	16	45	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>		-	5	30	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>		-	7	45	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>		-	5	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	1.3	1.65	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>		-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 11</a>		0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C		-	0.1	0.5	mA
<b>Dynamic characteristics</b>							
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit		100	250	-	V/μs
dV <sub>com</sub> /dt	rate of change of commutating voltage	V <sub>D</sub> = 400 V; T <sub>j</sub> = 95 °C; dI <sub>com</sub> /dt = 3.6 A/ms; I <sub>T</sub> = 6 A; gate open circuit		-	20	-	V/μs
t <sub>gt</sub>	gate-controlled turn-on time	I <sub>TM</sub> = 12 A; V <sub>D</sub> = 600 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> /dt = 5 A/μs		-	2	-	μs

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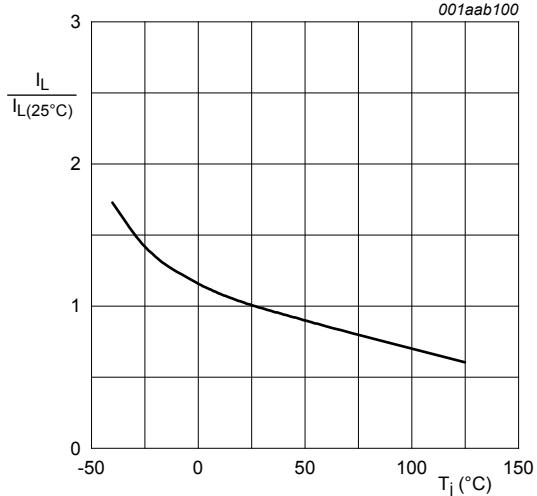
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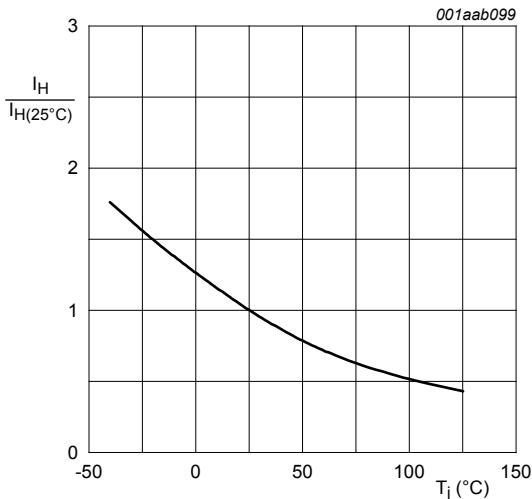


- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+
- (4) T2- G+

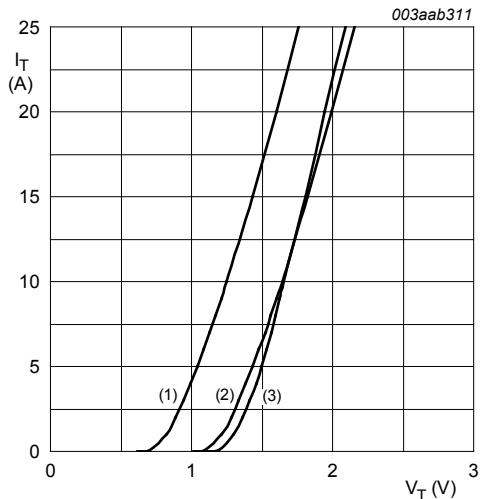
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



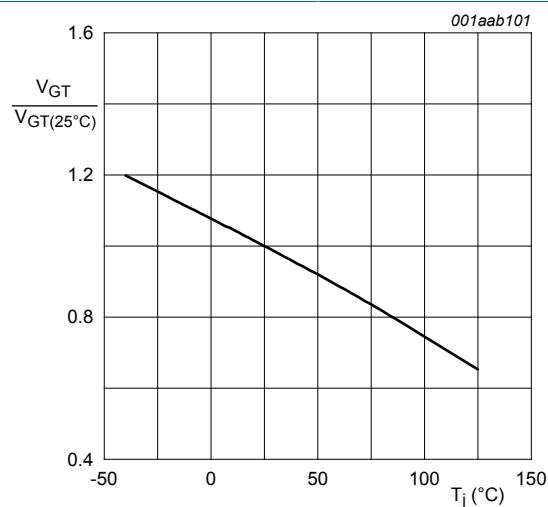
**Fig. 9. Normalized holding current as a function of junction temperature**



$$V_o = 1.26 \text{ V}; R_s = 0.0378 \Omega$$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

**NXP Semiconductors****BT236X-600****4Q Triac****Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

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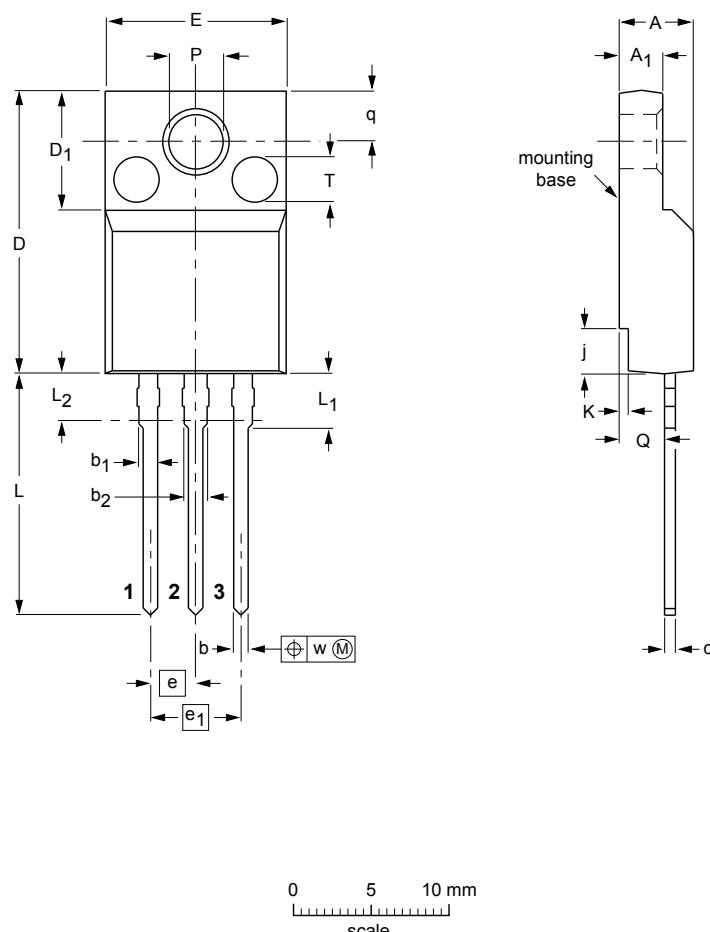
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### 11. Package outline

Plastic single-ended package; isolated heatsink mounted;  
 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



#### DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	e <sub>1</sub>	j	K	L	L <sub>1</sub>	L <sub>2</sub> <sup>(1)</sup> max.	P	Q	q	T <sup>(2)</sup>	w
mm	4.6	2.9	0.9	1.1	1.4	0.7	15.8	6.5	10.3	2.54	5.08	2.7	0.6	14.4	3.30	3	3.2	2.6	3.0	2.5	0.4
	4.0	2.5	0.7	0.9	1.0	0.4	15.2	6.3	9.7	2.54	5.08	1.7	0.4	13.5	2.79	3.0	3.0	2.3	2.6	2.5	0.4

#### Notes

1. Terminal dimensions within this zone are uncontrolled.
2. Both recesses are # 2.5 x 0.8 max. depth

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT186A		3-lead TO-220F				-02-04-09-06-02-14

Fig. 12. Package outline TO-220F (SOT186A)

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## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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